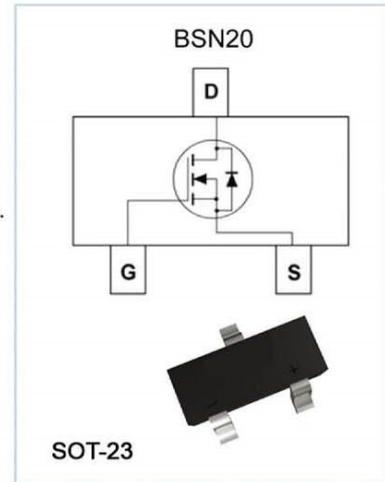


**N-Channel Enhancement Mode MOSFET**

**Feature**

- 50V/0.1A,  $R_{DS(ON)} = 3.5 \Omega$  (MAX) @ $V_{GS} = 5V$   $I_D = 0.1A$   
 $R_{DS(ON)} = 10 \Omega$  (MAX) @ $V_{GS} = 2.75V$ ,  $I_D = 0.1A$
- Super High dense cell design for extremely low  $R_{DS(ON)}$ .
- Reliable and Rugged.
- Low Threshold Voltage ( 0.5V—1.5V ) Make it Ideal for Low Voltage Applications.
- SOT-23 for Surface Mount Package.



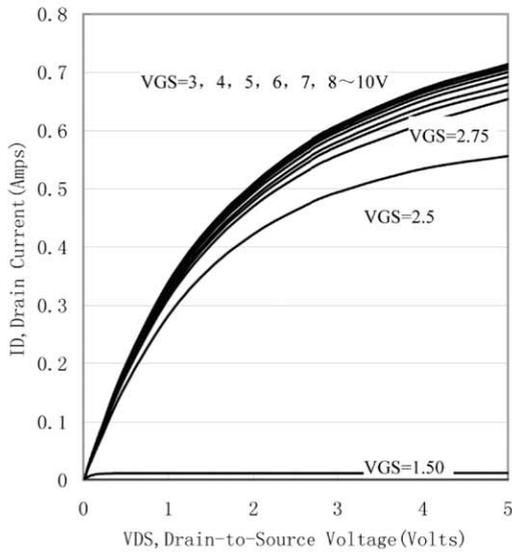
**Absolute Maximum Rating ( Ta = 25 °C Unless Otherwise Noted )**

Symbol	Parameter	Rating	Unit
$V_{DSS}$	Drain-Source Voltage	50	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	
$I_D$	Drain Current-Continuous	0.1	A

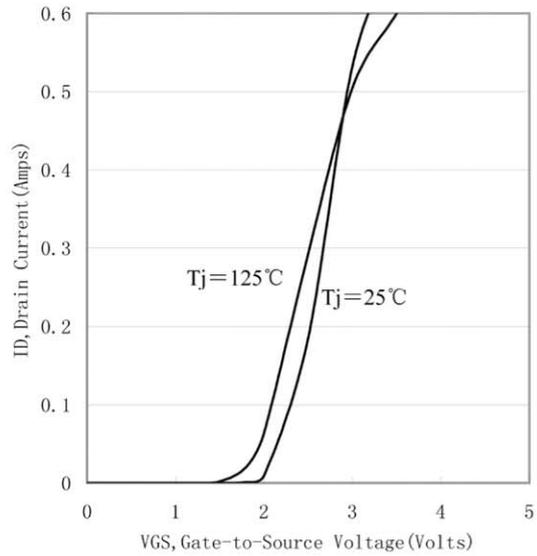
**Electrical Characteristics ( Ta = 25 °C Unless Otherwise Noted )**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0 V, I_{DS} = 250 \mu A$	50	-	-	V
		$V_{GS} = 0 V, I_{DS} = 10 \mu A$	50	-	-	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{DS} = 250 \mu A$	0.5	-	1.5	V
$I_{DSS}$	Drain Leakage Current	$V_{DS} = 50 V, V_{GS} = 0V$	-	-	500	nA
		$V_{DS} = 25 V, V_{GS} = 0V$	-	-	100	$\mu A$
$I_{GSS}$	Gate Leakage Current	$V_{GS} = \pm 20 V, V_{DS} = 0 V$	-	-	$\pm 300$	$\mu A$
$R_{DS(ON)}^a$	On-State Resistance	$V_{GS} = 5 V, I_{DS} = 0.2 A$	-	-	3.5	$\Omega$
		$V_{GS} = 2.75 V, I_{DS} = 0.2 A$	-	-	10	
$C_{iss}$	Input Capacitance	$V_{DS} = 10 V, V_{GS} = 0 V$ $f = 1 MHz$	-	21.8	40	$\mu F$
$C_{oss}$	Output Capacitance		-	5.6	15	
$C_{rss}$	Reverse Transfer Capacitance		-	3.3	10	
Diode Characteristics						
$V_{SD}$	Diode Forward Voltage	$I_{SD} = 0.2 A, V_{GS} = 0 V$	-	-	2.5	V

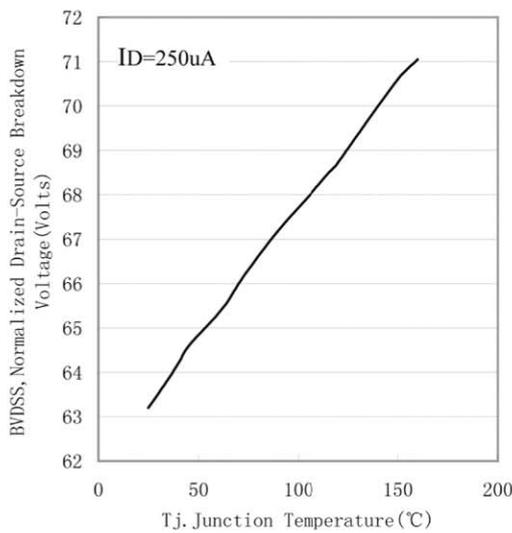
## Typical Characteristics



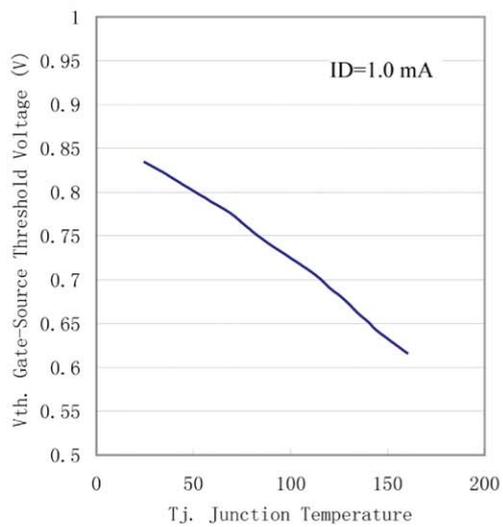
**Figure 1. Output Characteristics**



**Figure 2. Transfer Characteristics**

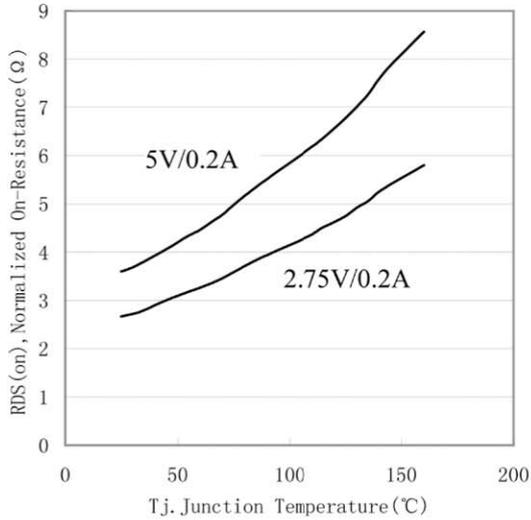


**Figure 3. Breakdown Voltage Variation with Temperature**

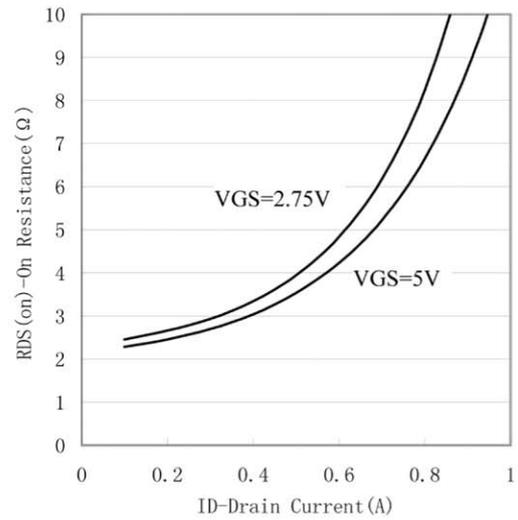


**Figure 4. Gate Threshold Variation with Temperature**

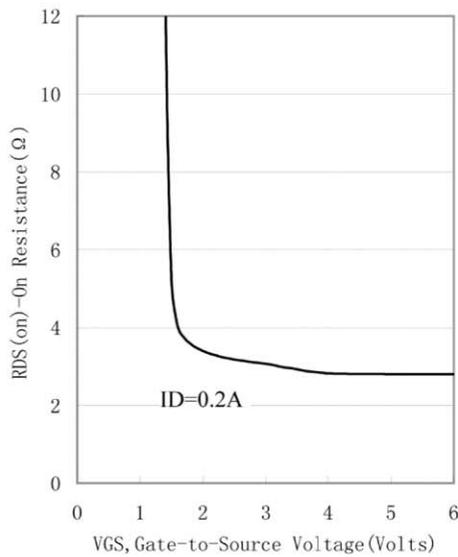
## Typical Characteristics



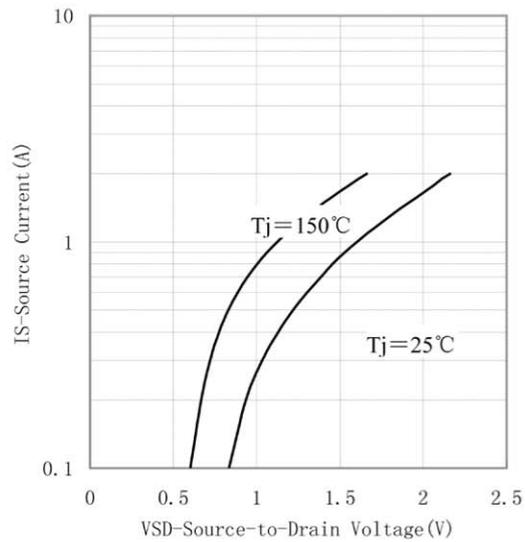
**Figure 5. On-Resistance Variation with Temperature**



**Figure 6. On-Resistance vs. Drain Current**



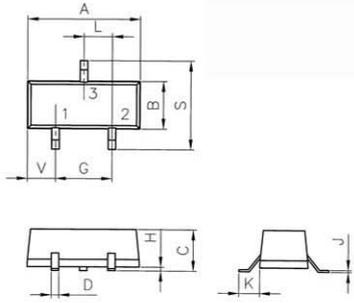
**Figure 7. On-Resistance vs. Gate-to-Source Voltage**



**Figure 8. Source-Drain Diode Forward Voltage**

## Outline dimensions

Unit: mm



	SOT-23	
	min	max
A	2.80	3.04
B	1.20	1.40
C	0.89	1.13
D	0.30	0.50
G	1.78	2.04
H	0.01	0.10
J	0.08	0.18
K	0.45	0.60
L	0.89	1.02
S	2.10	2.50
V	0.42	0.60